

(22) (((channel and (narrow or low) adj (bandgap or
 (7) (((channel and (narrow or low). adj (bandgap or (/
 (19) (narrow or low) adj (bandgap or (band adj gap))
 (18) ((narrow or low) adj (bandgap or (band adj gap))
 (10) (((narrow or low) adj (bandgap or (band adj gap)
 (10) (((narrow or low) adj (bandgap or (band adj gap
 (8) ((narrow or low) adj (bandgap or (band adj gap))
 (6) (channel near (narrow or low) adj (bandgap or (ba
 (35) (channel near3 (narrow or low) adj (bandgap or (/
 (54) (source or drain) near3 ((wide\$3 or high) adj (t
 (2) ((channel near3 (narrow or low) adj (bandgap or (/
 (13) ((source or drain) near3 ((wide\$3 or high) adj (/
 (115) ("SOI" or (insulat\$4 adj substrate)) and (((bar
 (4) ("SOI" or (insulat\$4 adj substrate)) and (((bar
 (8) ("SOI" or (insulat\$4 adj substrate)) and (((bar
 (3) ("5108370" | "5A20049" | "5A27962" | DN

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 DAS USPAT, US-PGPUB, EPO, IPOS, IBM, TDB Plurals
 Default operator: OR Highlight all hit terms initially

 (((((small or narrow or low) near3 (bandgap or (band adj gap)) near2
 channel)) and (gate and (source and drain) and transistor)) and
 (substrate and (dielectric or insulat\$4))) and (dielectric near3
 constant)

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040113210	20040617	9	Novel field effect transistor and method of fabrication	257/401	257/188; 257/333; 257/410;	<input type="checkbox"/>	Chau, Robert S. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040099966	20040527	9	Novel field effect transistor and method of fabrication	1/1	--	<input type="checkbox"/>	Chau, Robert S. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020185655	20021212	18	Ultra-linear multi-channel field effect transistor	257/192	--	<input type="checkbox"/>	Fahimulla, Ayub M. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5698869 A	19971216	90	Insulated-gate transistor having narrow-bandgap-source	257/192	257/347; 257/616; 257/66;	<input type="checkbox"/>	Yoshimi, Makoto et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>